

PNP resistor-equipped transistor; $R1 = 1 k\Omega$, $R2 = 10 k\Omega$ Rev. 1 — 21 June 2012Product data

Product data sheet

1. **Product profile**

1.1 General description

PNP Resistor-Equipped Transistor (RET) in a leadless ultra small DFN1006B-3 (SOT883B) Surface-Mounted Device (SMD) plastic package.

NPN complement: PDTC113ZMB.

1.2 Features and benefits

- 100 mA output current capability
- Reduces component count
- Built-in bias resistors
- Reduces pick and place costs

1.3 Applications

- Low-current peripheral driver
- Control of IC inputs

- Simplifies circuit design
- AEC-Q101 qualified
- Leadless ultra small SMD plastic package
- Low package height of 0.37 mm
- Replaces general-purpose transistors in digital applications
- Mobile applications

1.4 Quick reference data

Table 1.	Quick reference data					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{CEO}	collector-emitter voltage	open base	-	-	-50	V
lo	output current		-	-	-100	mA
R1	bias resistor 1 (input)	T _{amb} = 25 °C	0.7	1	1.3	kΩ
R2/R1	bias resistor ratio		8	10	12	



PNP resistor-equipped transistor; $R1 = 1 k\Omega$, $R2 = 10 k\Omega$

2. Pinning information

Table 2.	Pinning	j information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	I	input (base)		
2	G	GND (emitter)		
3	0	output (collector)	2 Transparent top view DFN1006B-3 (SOT883B)	1 R1 R2 sym003

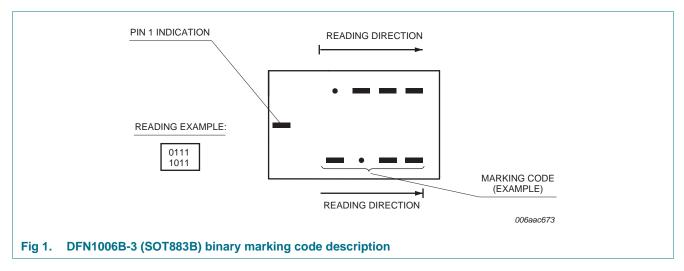
3. Ordering information

Table 3. Ordering information							
Type number	Package						
	Name	Description	Version				
PDTA113ZMB	DFN1006B-3	Leadless ultra small plastic package; 3 solder lands; body 1.0 x 0.6 x 0.37 mm	SOT883B				

4. Marking

Table 4.	Marking codes
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Type number	Marking code
PDTA113ZMB	0001 1101



PNP resistor-equipped transistor; R1 = 1 k Ω , R2 = 10 k Ω

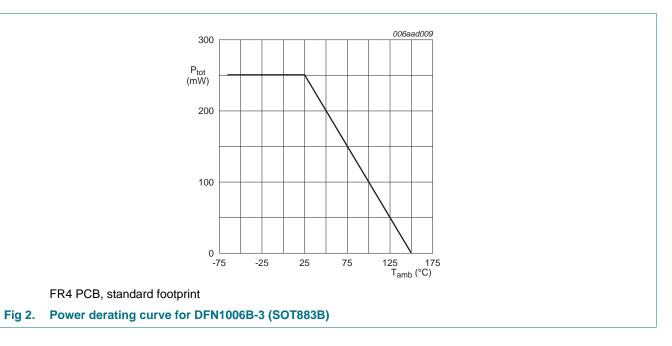
5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{CBO}	collector-base voltage	open emitter		-	-50	V
V _{CEO}	collector-emitter voltage	open base		-	-50	V
V _{EBO}	emitter-base voltage	open collector		-	-5	V
VI	input voltage	positive		-	5	V
		negative		-	-10	V
lo	output current			-	-100	mA
I _{CM}	peak collector current	pulsed; t _p ≤ 1 ms		-	-100	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	<u>[1]</u>	-	250	mW
Tj	junction temperature			-	150	°C
T _{amb}	ambient temperature			-65	150	°C
T _{stg}	storage temperature			-65	150	°C

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

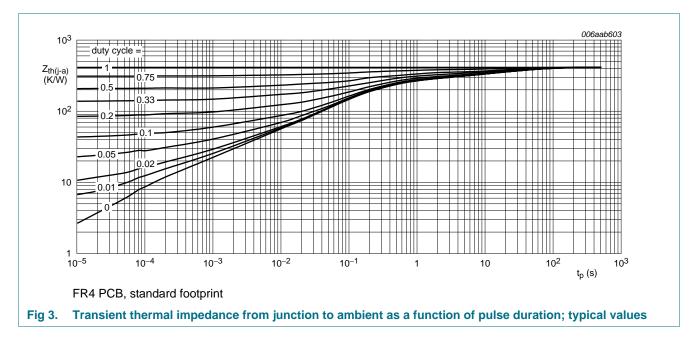


PNP resistor-equipped transistor; R1 = 1 k Ω , R2 = 10 k Ω

6. Thermal characteristics

Table 6.	Thermal characteristics						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	<u>[1]</u>	-	-	500	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

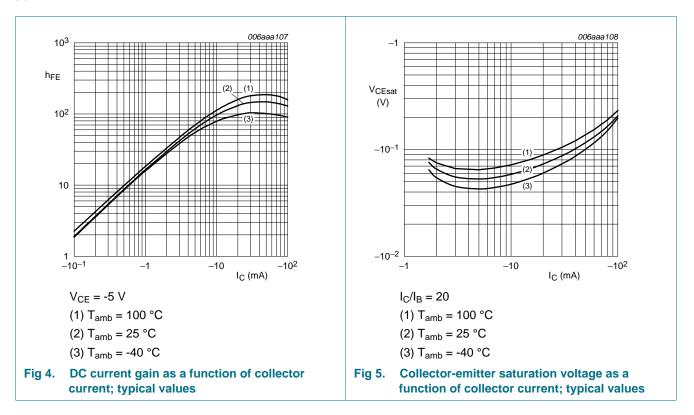


PNP resistor-equipped transistor; R1 = 1 k Ω , R2 = 10 k Ω

7. Characteristics

Characteristics						
Parameter	Conditions		Min	Тур	Max	Unit
collector-base cut-off current	V_{CB} = -50 V; I _E = 0 A; T _{amb} = 25 °C		-	-	-100	nA
collector-emitter cut-off	$V_{CE} = -30 \text{ V}; \text{ I}_{B} = 0 \text{ A}; \text{ T}_{amb} = 25 \text{ °C}$		-	-	-1	μA
current	V_{CE} = -30 V; I _B = 0 A; T _j = 150 °C		-	-	-5	μA
emitter-base cut-off current	V_{EB} = -5 V; I _C = 0 A; T _{amb} = 25 °C		-	-	-800	μA
DC current gain	V_{CE} = -5 V; I _C = -5 mA; T _{amb} = 25 °C		35	-	-	
collector-emitter saturation voltage	I_{C} = -10 mA; I_{B} = -0.5 mA; T_{amb} = 25 °C		-	-	-150	mV
off-state input voltage	V_{CE} = -5 V; I_C = -100 $\mu A;$ T_{amb} = 25 °C		-	-0.65	-0.3	V
on-state input voltage	V_{CE} = -300 mV; I _C = -20 mA; T _{amb} = 25 °C		-2.5	-0.95	-	V
bias resistor 1 (input)	T _{amb} = 25 °C		0.7	1	1.3	kΩ
bias resistor ratio			8	10	12	
collector capacitance	V_{CB} = -10 V; I _E = 0 A; i _e = 0 A; f = 1 MHz; T _{amb} = 25 °C		-	-	2	pF
transition frequency	V_{CE} = -5 V; I _C = -10 mA; f = 100 MHz; T _{amb} = 25 °C	<u>[1]</u>	-	180	-	MHz
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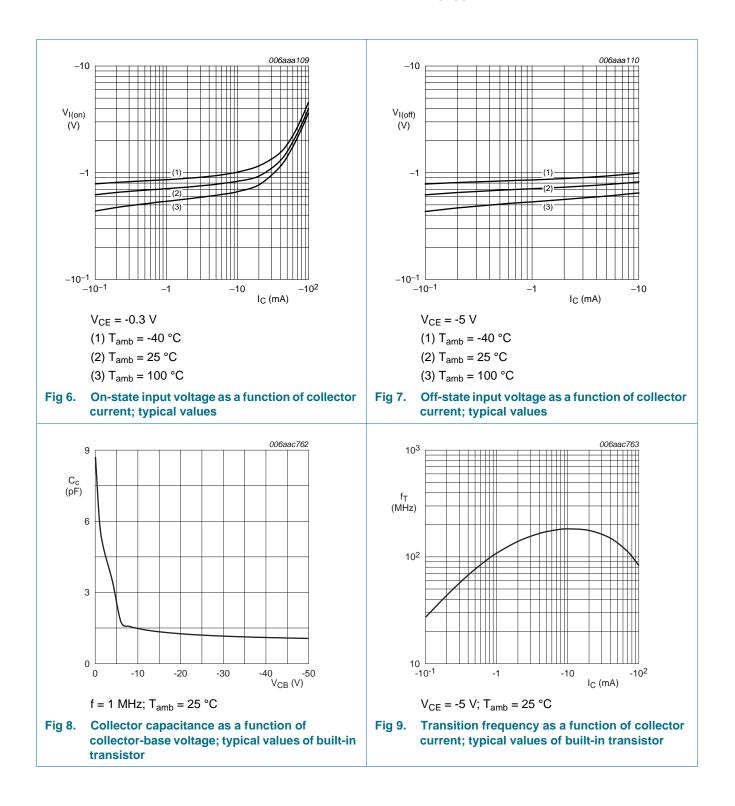
[1] Characteristics of built-in transistor.



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PDTA113ZMB

PNP resistor-equipped transistor; R1 = 1 k Ω , R2 = 10 k Ω



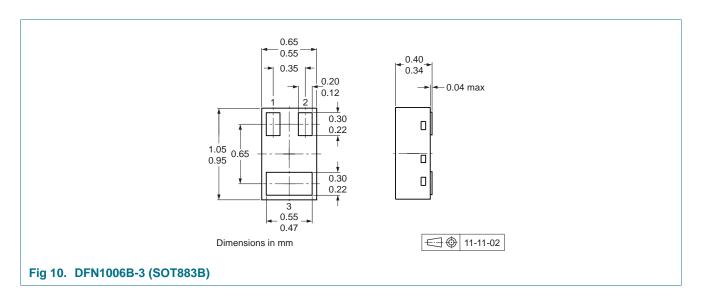
PNP resistor-equipped transistor; R1 = 1 k Ω , R2 = 10 k Ω

8. Test information

8.1 Quality information

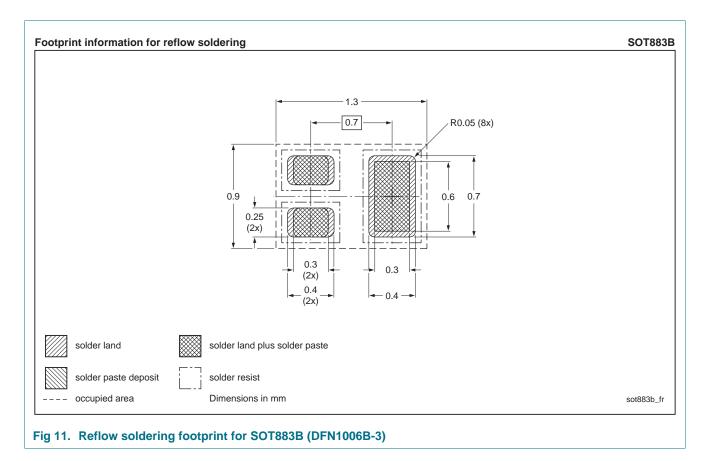
This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

9. Package outline



PNP resistor-equipped transistor; $R1 = 1 k\Omega$, $R2 = 10 k\Omega$

10. Soldering



PNP resistor-equipped transistor; R1 = 1 k Ω , R2 = 10 k Ω

11. Revision history

Table 8. Revision h	nistory			
Document ID	Release date	Data sheet status	Change notice	Supersedes
PDTA113ZMB v.1	20120621	Product data sheet	-	-

PNP resistor-equipped transistor; R1 = 1 k Ω , R2 = 10 k Ω

12. Legal information

12.1 Data sheet status

Document status[1] [2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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